Octal Bus Buffer

The MC74VHC244 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology.

The MC74VHC244 is a noninverting 3-state buffer, and has two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 3.9 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.9 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V Machine Model > 200 V
- Chip Complexity: 136 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

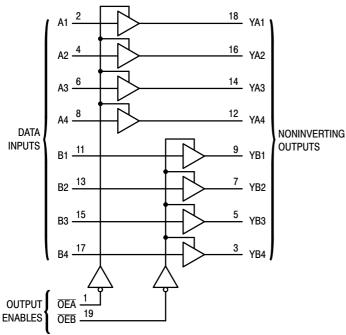


Figure 1. Logic Diagram



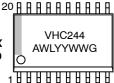
ON Semiconductor™

http://onsemi.com

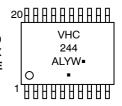
MARKING DIAGRAMS



SOIC-20 DW SUFFIX CASE 751D





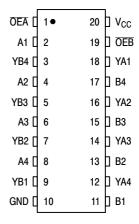


VHC244 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information in the Ordering Information Table on page 2 of this data sheet.

FUNCTION TABLE

INP	OUTPUTS	
OEA, OEB	A, B	YA, YB
L	L	L
L	Н	Н
Н	Х	Z

ORDERING INFORMATION

Device	Package	Shipping [†]	
MC74VHC244DWR2G	SOIC-20 WB (Pb-Free)	1000/Tape & Reel	
MC74VHC244DTG		75 Units/Rail	
MC74VHC244DTR2G	TSSOP-20 (Pb-Free)	2500/Tape & Reel	
NLV74VHC244DTR2G*	(2500/Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS (Note 1)

Symbol	Р	arameter	Value	Unit
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	Digital Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} +0.5	٧
I _{IK}	Input Diode Current		-20	mA
lok	Output Diode Current		±20	mA
I _{OUT}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	5	±75	mA
P _D	Power Dissipation in Still Air	SOIC TSSOP	500 450	mW
T _{STG}	Storage Temperature Range		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 >2000	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±300	mA
θ_{JA}	Thermal Resistance, Junction-to-Amb	ient SOIC TSSOP	96 128	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} . Unused inputs must always be tied to an appropriate logic voltage

- 2. Tested to EIA/JESD22-A114-A
- 3. Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage		0	V _{CC}	V
T _A	Operating Temperature Range, all Package Types		-55	125	°C
t _r , t _f	Input Rise or Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

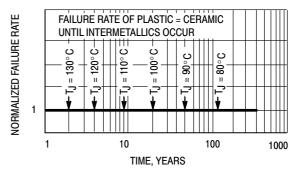


Figure 2. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	1	Γ _A = 25°	С	T _A ≤	85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level		2.0	1.5			1.5	1.5	1.5		٧
	Input Voltage		3.0 to 5.5	V _{CCX} 0.7			V _{CCX} 0.7	V _{CCX} 0.7	V _{CCX} 0.7		
V_{IL}	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0 to 5.5			V _{CCX} 0.3		V _{CCX} 0.3		V _{CCX} 0.3	
V _{OH}	Maximum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		٧
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = 4 \text{ mA}$ $I_{OH} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{OZ}	Maximum 3-State Leakage Current	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5			±0.25		±2.5		±2.5	μΑ
Icc	Maximum Quiescent Supply Current (per package)	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				T _A = 25°	·C	T _A ≤	85°C		C ≤ T _A 25°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or	$V_{CC} = 3.3 \pm 0.3 \ V \begin{array}{c} C_L = 15 \\ C_L = 50 \end{array}$		5.8 8.3	8.4 11.9	1.0 1.0	10.0 13.5	1.0 1.0	11.0 14.5	ns
	B to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V} \begin{array}{c} C_L = 15 \\ C_L = 50 \end{array}$		3.9 5.4	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	7.5 9.5	
t _{PZL} , t _{PZH}	Output Enable Time OEA to YA or	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		6.6 9.1	10.6 14.1	1.0 1.0	12.5 16.0	1.0 1.0	13.5 17.0	ns
	OEB to YB	$\label{eq:VCC} $		4.7 6.2	7.3 9.3	1.0 1.0	8.5 10.5	1.0 1.0	9.5 11.5	
t _{PLZ} , t _{PHZ}	Output Disable Time OEA to YA or	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 \ V C_L = 50 \\ R_L &= 1 \ k \Omega \end{aligned}$	ρF	10.3	14.0	1.0	16.0	1.0	17.0	ns
	OEB to YB		ρF	6.7	9.2	1.0	10.5	1.0	11.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50$ (Note 6)	ρF		1.5		1.5		1.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50$ (Note 6)	ρF		1.0		1.0		1.5	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)			6						pF

		Typical @ 25°C, V _{CC} = 5.0V		
C_{PD}	Power Dissipation Capacitance (Note 7)	19	pF	

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$, $C_L = 50 \text{ pF}$, $V_{CC} = 5.0 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.6	0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.6	-0.9	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

SWITCHING WAVEFORMS

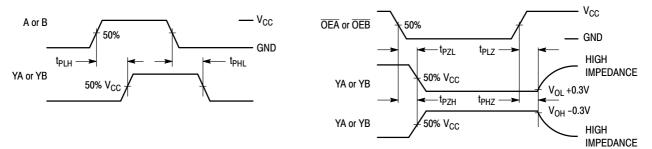
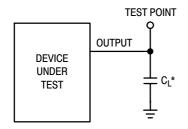


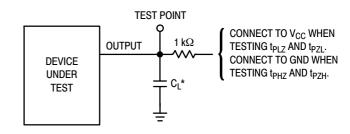
Figure 3. Switching Waveform

Figure 4. Switching Waveform

TEST CIRCUITS



*Includes all probe and jig capacitance



*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 6. Test Circuit

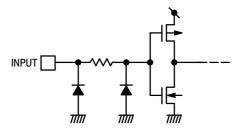
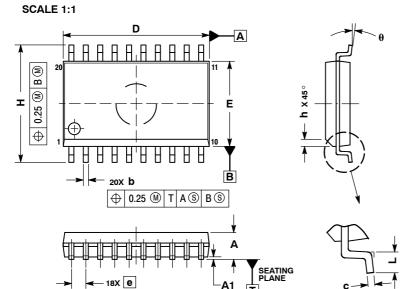


Figure 7. Input Equivalent Circuit



SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015

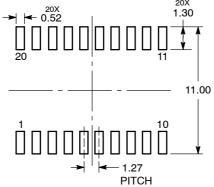


NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

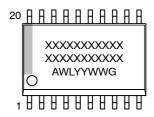
	MILLIMETERS				
DIM	MIN MAX				
Α	2.35	2.65			
A1	0.10	0.25			
b	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
A	0 °	7 °			

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"		
DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1	

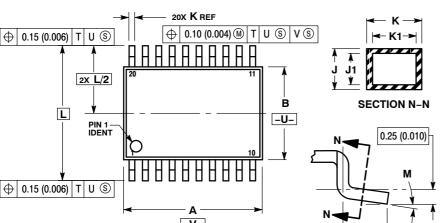
are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor and ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

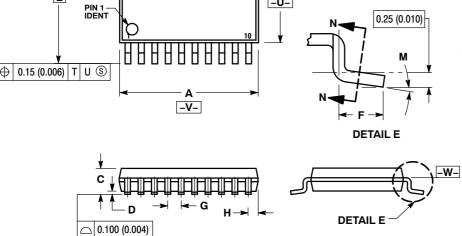
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

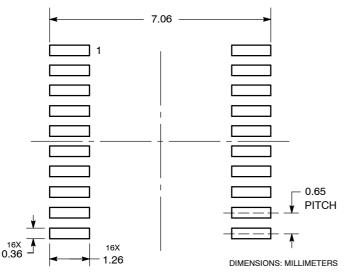
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION.
- SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

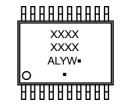
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ĺ	6.40	6.40 BSC		BSC	
M	٥°	80	0.0	80	

SOLDERING FOOTPRINT

-T- SEATING



GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP-20 WB	•	PAGE 1 OF 1

ON Semiconductor and III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Buffers & Line Drivers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

LXV200-024SW 74AUP2G34FW3-7 HEF4043BP PI74FCT3244L MC74HCT365ADTR2G Le87401NQC Le87402MQC 028192B
042140C 051117G 070519XB NL17SZ07P5T5G NLU1GT126AMUTCG 74AUP1G17FW5-7 74LVC2G17FW4-7 CD4502BE 59628982101PA 5962-9052201PA 74LVC1G125FW4-7 NL17SH17P5T5G NL17SH125P5T5G NLV37WZ07USG RHRXH162244K1
74AUP1G34FW5-7 74AUP1G07FW5-7 74LVC2G126RA3-7 NLX2G17CMUTCG 74LVCE1G125FZ4-7 Le87501NQC 74AUP1G126FW5-7 TC74HC4050AP(F) 74LVCE1G07FZ4-7 NLX3G16DMUTCG NLX2G06AMUTCG NLVVHC1G50DFT2G NLU2G17AMUTCG
LE87100NQC LE87290YQC LE87290YQCT LE87511NQC LE87511NQCT LE87557NQC LE87557NQCT LE87614MQC
LE87614MQCT 74AUP1G125FW5-7 NLU2G16CMUTCG MC74LCX244MN2TWG NLV74VHC125DTR2G NL17SG126DFT2G